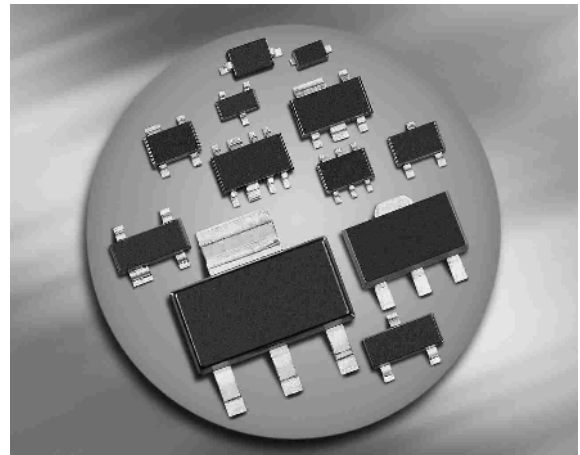
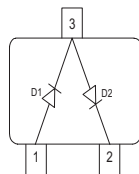
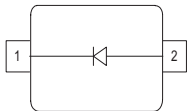


**Silicon PIN Diode**

- For low loss RF switches and attenuators
- Very low capacitance at zero volt reverse bias at frequencies above 1 GHz (typ. 0.25 pF)
- Low forward resistance (typ. 1.5  $\Omega$  @ 5mA)
- Low harmonics
- Pb-free (RoHS compliant) package


**BAR67-02V**
**BAR67-04**


Type	Package	Configuration	$L_S$ (nH)	Marking
BAR67-02V	SC79	single	0.6	T
BAR67-04	SOT23	series	1.8	PMs

**Maximum Ratings at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	150	V
Forward current	$I_F$	200	mA
Total power dissipation	$P_{tot}$		mW
$T_S \leq 118^\circ\text{C}$ , BAR67-02V		250	
$T_S \leq 25^\circ\text{C}$ , BAR67-04		250	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-55 ... 125	
Storage temperature	$T_{stg}$	-55 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
BAR67-02V		$\leq 115$	
BAR67-04		$\leq 290$	

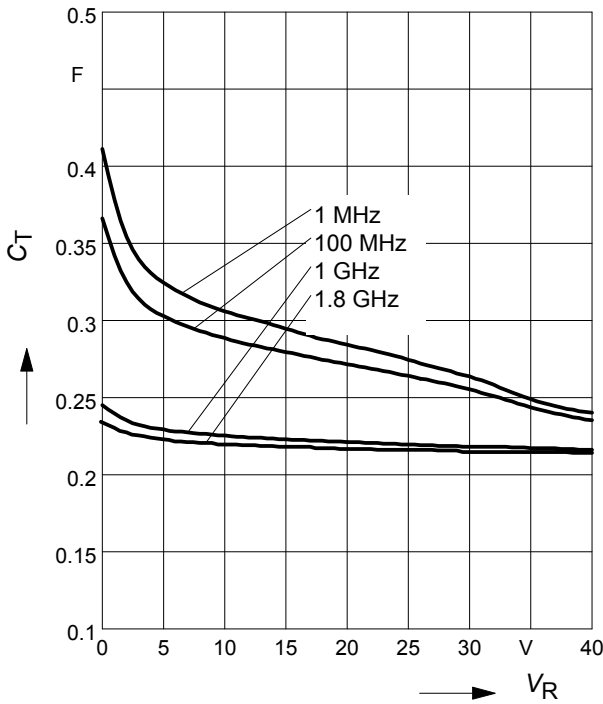
<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Breakdown voltage $I_{(BR)} = 5 \mu\text{A}$	$V_{(BR)}$	150	-	-	V
Reverse current $V_R = 100 \text{ V}$	$I_R$	-	-	20	nA
Forward voltage $I_F = 50 \text{ mA}$	$V_F$	-	0.95	1.2	V
<b>AC Characteristics</b>					
Diode capacitance $V_R = 5 \text{ V}, f = 1 \text{ MHz}$ $V_R = 0 \text{ V}, f = 100 \text{ MHz}$ $V_R = 0 \text{ V}, f = 1 \text{ GHz}$ $V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$	$C_T$	-	0.35	0.55	pF
Reverse parallel resistance $V_R = 0 \text{ V}, f = 100 \text{ MHz}$ $V_R = 0 \text{ V}, f = 1 \text{ GHz}$ $V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$	$R_P$	-	25	-	k $\Omega$
Forward resistance $I_F = 5 \text{ mA}, f = 100 \text{ MHz}$ $I_F = 10 \text{ mA}, f = 100 \text{ MHz}$	$r_f$	-	1.5	1.8	$\Omega$
Charge carrier life time $I_F = 10 \text{ mA}, I_R = 6 \text{ mA}$ , measured at $I_R = 3 \text{ mA}$ , $R_L = 100 \Omega$	$\tau_{rr}$	-	700	-	ns
I-region width	$W_I$	-	13	-	$\mu\text{m}$

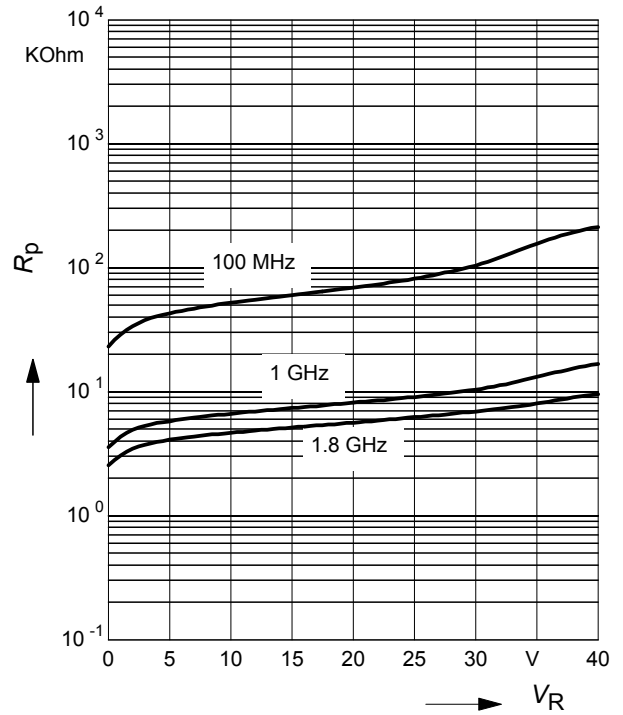
**Diode capacitance  $C_T = f(V_R)$**

$f =$  Parameter



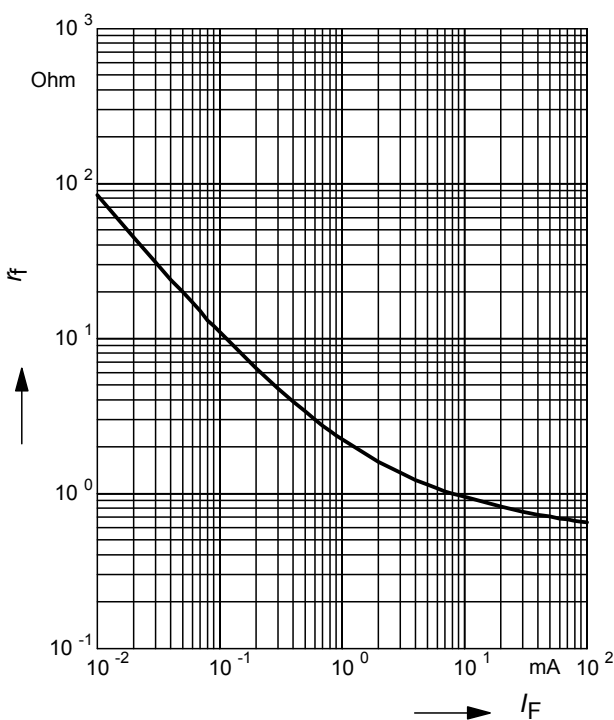
**Reverse parallel resistance  $R_P = f(V_R)$**

$f =$  Parameter



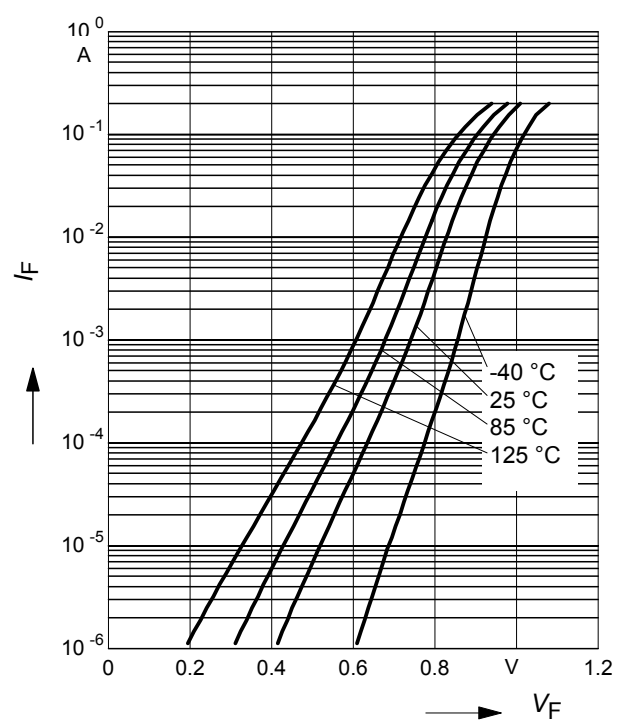
**Forward resistance  $r_f = f(I_F)$**

$f = 100\text{MHz}$



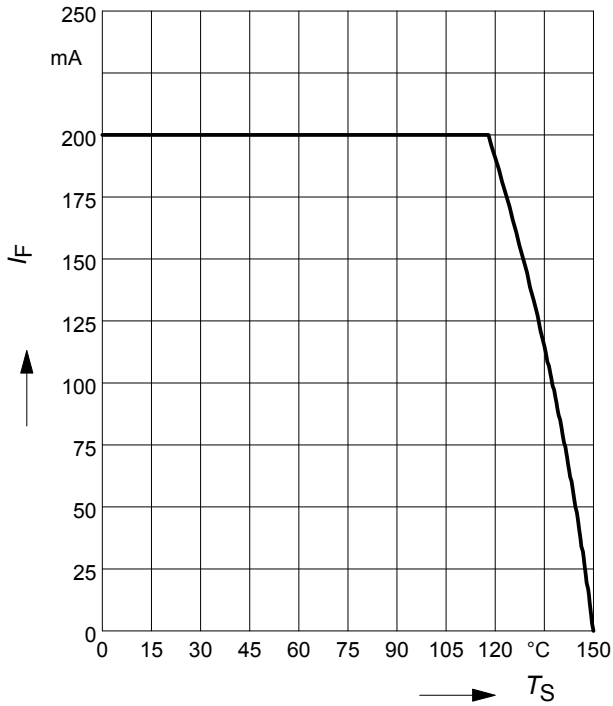
**Forward current  $I_F = f(V_F)$**

$T_A =$  Parameter



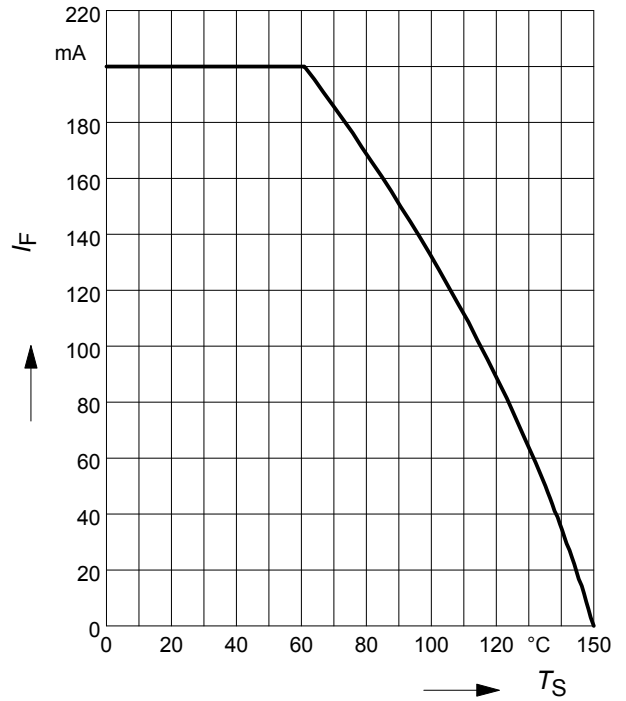
**Forward current  $I_F = f(T_S)$**

BAR67-02V



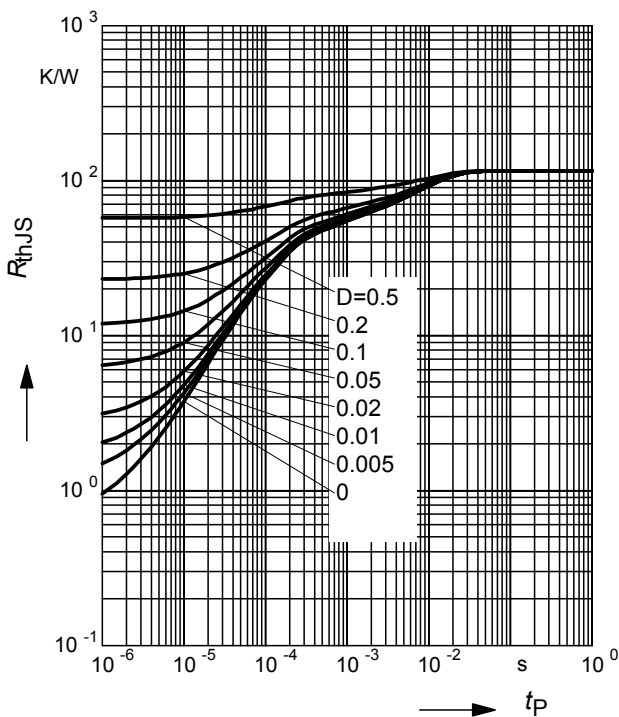
**Forward current  $I_F = f(T_S)$**

BAR67-04



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

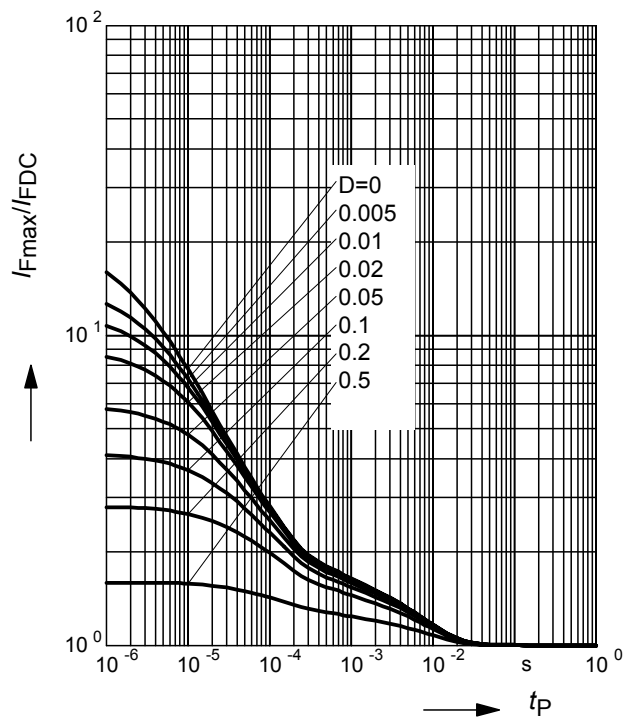
BAR67-02V



**Permissible Pulse Load**

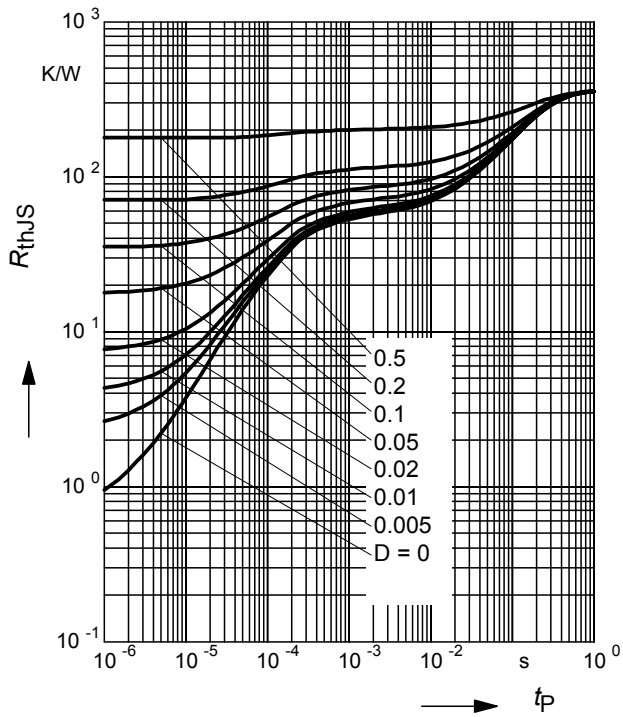
$I_{Fmax} / I_{FDC} = f(t_p)$

BAR67-02V

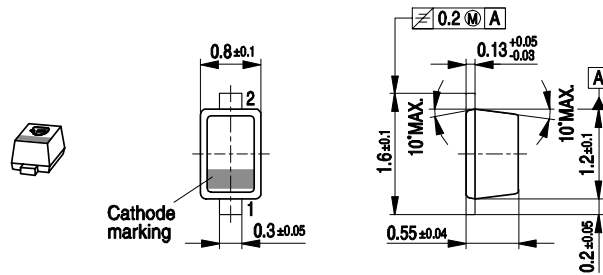


Permissible Puls Load  $R_{thJS} = f(t_p)$

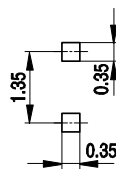
BAR67-04



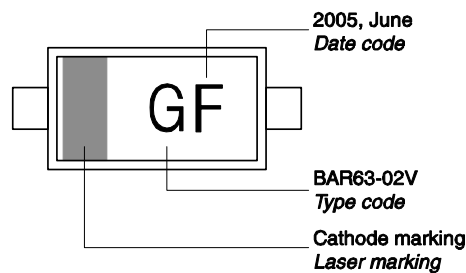
### Package Outline



### Foot Print

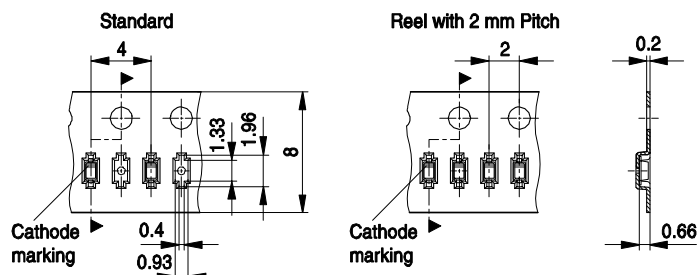


### Marking Layout (Example)



### Standard Packing

- Reel ø180 mm = 3.000 Pieces/Reel
- Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)
- Reel ø330 mm = 10.000 Pieces/Reel

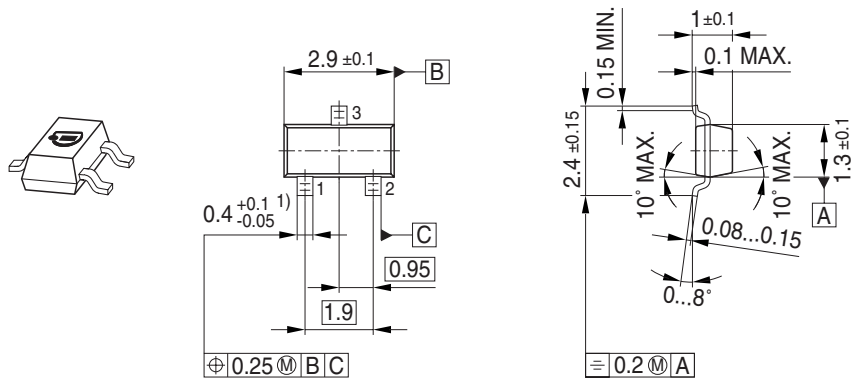


Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

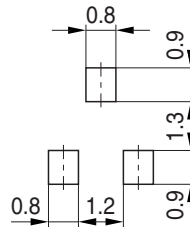
1) New Marking Layout for SC75, implemented at October 2005.

Package Outline

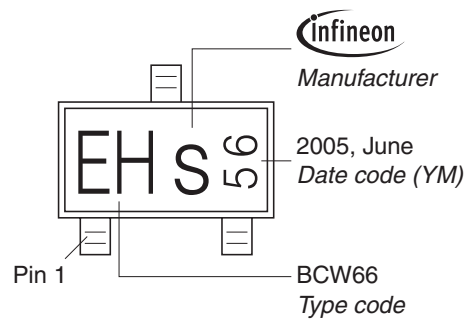


1) Lead width can be 0.6 max. in dambar area

Foot Print

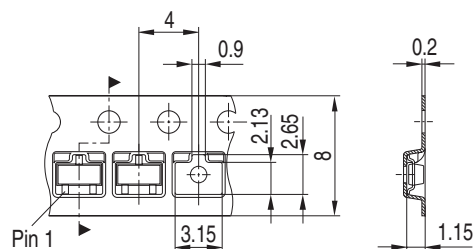


Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel





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